NSN 5961-01-246-4594

Semiconductor Device Set - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-246-4594

Inclosure Material: Metal all transistor **Overall Length:** 1.245 inches all transistor **Mounting Facility Quantity:** 1 all transistor **Internal Configuration:** Junction contact all transistor Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-61 all transistor **Internal Junction Configuration:** Npn all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Threaded stud all transistor **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.687 inches all transistor Thread Size: 0.250 inches all transistor **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 550.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter all transistor and 450.0 collector-to-emitter substaining voltage, with specified circuit between base and emitter all transistor **Voltage Tolerance In Percent:** -5.0/+5.0 all transistor **Current Rating Per Characteristic:** 50.00 microamperes zero-gate-voltage source current preset all transistor **Power Rating Per Characteristic:** 75.0 watts small-signal input power, common-collector absolute all transistor **Transfer Ratio:** 90.0 static forward current transfer ratio, common-emitter all transistor

Precious Material:Gold

Thread Series Designator:

Leads external surfaces gold

Precious Material And Location:

Unf all transistor

NSN 5961-01-246-4594

Semiconductor Device Set - Page 2 of 2



Terminal Type Ar	nd Quantity:
------------------	--------------

3 tab, solder lug all transistor

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0